

Attorney Docket No.: 15675P322C
Express Mail No.: EV339912409US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

CLAUDE CHAPPERT, ET AL.

For: Magnetic Etching Process, Especially For Magnetic Or
Magnetooptic Recording

Examiner: Angebranndt, M.J.

Art Unit: 1756

Continuation of Application:

Application No.: 09/600,546

Filing Date: July 12, 2000

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with 37 CFR 1.56, Applicant hereby discloses the prior art references that have been submitted and/or cited in the following related application/patent:

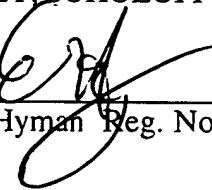
Serial No.	Filing Date	Patent No.	Issue Date
09/600,546	July 12, 2000	---	---

Form PTO/SB/08B(substitute for form 1449A/PTO) is enclosed herewith. Copies of the references are not provided as permitted by 37 CFR 1.98(d).

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN

Date: 4/19/01

By: 

Eric S. Hyman Reg. No. 30,139

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Form PTO-1449 (Modified)		Atty Docket No. 15675.P322	Serial No. 09/600,546
<i>List of Patents & Publications Statement</i>		Applicant(s): C. Chappert	
(Use several sheets if necessary)		Filing Date: 7/12/00	Group No. 1756

U.S. PATENT DOCUMENTS

Exam. Initials	Document Number	Date	Name	Class	Sub-class	Filing Date (if appropriate)
AA						
AB						
AJ						
AK						

FOREIGN PATENT DOCUMENTS

Exam. Initials	Document Number	Date	Country	Class	Sub-class	Translation Yes	No
AL	JP0129699	11/1989	Japan	—	—	X	
AQ							

OTHER ART (Including Title, Author, Date, Pertinent Pages, etc.)

Exam. Initials	Document Identification	
AR	Xiao J Q. et al.: "Effects of ar-Ion implantation and annealing on structural and magnetic properties of CO/PD multilayers" Journal of applied Physics, vol. 76, no. 10, part 02 11/15/94, pages 6081-6083	
AS	Amaral L. et al.: "Very Thin Fe/Ni modulation multilayer films under ion bombardment" Journal of Applied Physical vol. 81, no. 8, part 02B, April 15, 1997, pages 4773-4775	
AT	Gladyszewski G. et al.: "Modification of Structure, Electric and Magnetic Properties of Epitaxially Grown Ag(001)/FE(001) Superlattices" Journal of Magnetism and Magnetic Materials, vol. 156, no. 1/03, April 1, 1996, page 381-382	
AU	Choe G. et al.: "Effect of Ion Beam Mixing on Microstructure and Magnetic Properties of GD-Co Multilayer Films" Journal of Applied Physics, vol. 79, no. 8, part 02B, April 16, 1996	
AV	Schelp L. F. et al.: "Structural and Magnetic Behavior of AR+-Implanted Co/PD Multilayers: Interfacial Mixing" Journal of Applied Physics vol. 75, no. 10, part 01, May 15, 1994	

Examiner:

WJL

Date Considered:

11/14/01

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Notice of References Cited	Application/Control No. 09/600,546	Applicant(s)/Patent Under Reexamination CHAPPERT ET AL.	
	Examiner Martin J Angebranndt	Art Unit 1756	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification	
	A	US-4551908 ✓	11-1985	Nagasawa et al.	29	571
	B	US-4600488 ✓	07-1986	Imura et al.	204	298
	C	US-				
	D	US-				
	E	US-				
	F	US-				
	G	US-				
	H	US-				
	I	US-				
	J	US-				
	K	US-				
	L	US-				
	M	US-				

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification	
	N	62-297458 ✓	12-1987	Japan	****	--	--
	O						
	P						
	Q						
	R						
	S						
	T						

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kanayama et al., "Fine Pattern Definition with Atomic Intermixing Induced by Focused Ion Beam and Its Application to X-ray Mask Fabrication", J. Vac Sci. Technol. B, Vol 9(2) pp. 296-301 (4/1991)
	V ✓	Jung et al. "Atomic Transport by Ion Beam Mixing in the Radiation Enhanced Diffusion Region", Mat. Res. Soc. Symp. Proc. Vol. 354 pp. 21-26 (1995)
	W	Steckl et al. "Review of Focused ion beam mixing for the fabrication of GaAs based optoelectronic devices", J. Vac. Sci. Technol. B, Vol 13(6) pp 2570-2575 (11/12-1995)
	X ✓	Gamo et al., "Recent advances in the Application of focussed ion beams", Mat. Res. Soc. Symp. Proc., Vol. 45 pp. 223-234 (1985)

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination CHAPPERT ET AL.	
		Examiner Martin J Angebranndt	Art Unit 1756	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
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	F	US-			
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	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	2773632	07-1999	France	Chappert et al.	***
	O	99/35657	07-1999	WIPO	Chappert et al.	***
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Copy of Specification denoted WO 99/35657 in upper left and 1 in upper right.
	V	Copy of specification denoted 2 in upper right hand corner.
	W	
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